

ELECTROPHYSICAL AND PHOTOELECTRICAL
PROPERTIES OF DEFORMED CRYSTALS

n-Hg_{1-x}Cd_xTe

I.S. Virt, B.P. Koman¹, D.I. Tsyutsyura, Yu.O. Ugrin

I. Franko Drogobych State Pedagogical University
(24, Franko Str, Drogobych 79720, Ukraine),

¹I. Franko National Lviv University
(8, Kyryl i Mefodiy Str., Lviv 79005, Ukraine)

S u m m a r y

The electrophysical and photoelectrical investigation of plastically deformed crystals n-Hg_{1-x}Cd_xTe is carried out. It is shown that the recombination contribution of defects appeared is determined under these conditions by local levels with $E_d = 52$ meV. The carrier transport is realized along channels with a more narrow band-gap and increases the electron concentration.